

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3977	Ion adj traps	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:24
L2	14	1 and ( fabric\$5 near4 dielectric )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:30
L3	40	1 and ( fabric\$5 near4 semiconductor )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:47
L4	8	3 and ( etch\$3 near4 electrode )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:31
L5	20	3 and ( form\$3 near4 electrode )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:32
L6	8	1 and ( alternate near4 layers )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:23
L7	2091922	1 and fabrication or manufacturing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:58
L8	505	1 and ( fabrication or manufacturing )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:59

L9	505	8 and ( ion near4 traps )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:59
L10	244	1 and ( fabrication or manufacturing near4 ion adj traps )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:00
L11	0	10 and ( alternate near4 conducting adj layers )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:01
L12	2	10 and ( etch\$3 near4 cavity )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:06
L13	4	"6,469,298"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:10
L14	14	"6,459,080"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:11
L15	15	"5,793,091"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:12
L16	8	1 and ( alternate near6 layers )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:31

L17	241	Ion adj traps and fabrication	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:32
L18	6	17 and ( alternate near4 layers )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 15:07
L19	3482	((250/299,292,282,288,) or (216/2, ) or (313/256,)).CCLS.	USPAT	OR	OFF	2005/08/18 15:07
L20	19	19 and ( alternate near4 layers )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 15:09
L21	1770	19 and ( etch\$3 near4 cavity or electrode )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 15:08
L22	15	21 and ( alternate near4 layers )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 15:09